

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

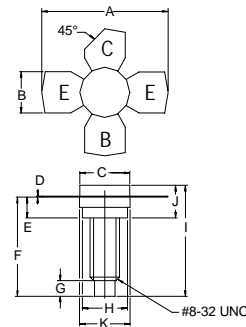
The **ASI TPV596A** is designed for MATV amplifiers up to 860 MHz and 500 mW band V TV transposer stages.

FEATURES:

- Difused emitter ballast resistors
- $P_G = 12$ dB at 0.5 W/ 860 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	0.7 A
V_{CBO}	45 V
V_{CEO}	24 V
V_{EBO}	3.5 V
P_{DISS}	8.75 W @ $T_C = 25$ °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	20 °C/W

PACKAGE STYLE .280 4L STUD


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	1.010 / 25.65	1.055 / 26.80
B	.220 / 5.59	.230 / 5.84
C	.270 / 6.86	.285 / 7.24
D	.003 / 0.08	.007 / 0.18
E	.117 / 2.97	.137 / 3.48
F	.572 / 14.53	
G	.130 / 3.30	
H	.245 / 6.22	.255 / 6.48
I	.640 / 16.26	
J	.175 / 4.45	.217 / 5.51
K	.275 / 6.99	.285 / 7.24

CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 1.0$ mA			45			V
BV_{CEO}	$I_C = 20$ mA			24			V
BV_{EBO}	$I_E = 4.0$ mA			3.5			V
I_{CBO}	$V_{CB} = 28$ V					1.0	mA
h_{FE}	$V_{CE} = 5.0$ V	$I_C = 100$ mA		15		120	---
C_{OB}	$V_{CB} = 28$ V $f = 1.0$ MHz					5.0	pF
P_G	$V_{CE} = 20$ V	$I_E = 220$ mA	$f = 860$ MHz	11.5	12		dB
IMD_1	$P_{OUT} = 0.5$ W	$P_{IN} = 50$ mW				-58	dB